

# MOSFET – P-Channel, POWERTRENCH®

**-20 V, -56 A, 6.5 mΩ**

## NTTFS007P02P8

### General Description

This P-Channel MOSFET is produced using onsemi's advanced POWERTRENCH process that has been optimized for  $R_{DS(on)}$ , switching performance and ruggedness.

### Features

- Max  $R_{DS(on)}$  = 6.5 mΩ at  $V_{GS} = -4.5$  V,  $I_D = -14$  A
- Max  $R_{DS(on)}$  = 9.8 mΩ at  $V_{GS} = -2.5$  V,  $I_D = -11$  A
- Max  $R_{DS(on)}$  = 20 mΩ at  $V_{GS} = -1.8$  V,  $I_D = -9$  A
- High Performance Trench Technology for Extremely Low  $R_{DS(on)}$
- High Power and Current Handling Capability in a Widely Used Surface Mount Package
- This Device is Pb-Free, Halide Free and is RoHS Compliant

### Applications

- Load Switch
- Battery Management
- Power Management
- Reverse Polarity Protection

### MOSFET MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

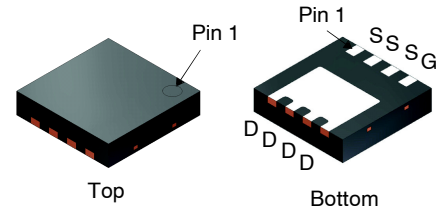
Symbol	Parameter	Ratings	Unit
$V_{DS}$	Drain to Source Voltage	-20	V
$V_{GS}$	Gate to Source Voltage	±8	V
$I_D$	Drain Current -Continuous, $T_C = 25^\circ\text{C}$ -Continuous, $T_A = 25^\circ\text{C}$ (Note 1a) -Pulsed (Note 3)	-56 -14 -226	A
$P_D$	Power Dissipation $T_C = 25^\circ\text{C}$ $T_A = 25^\circ\text{C}$ (Note 1a)	30 2.3	W
$T_J, T_{STG}$	Operating and Storage Junction Temperature Range	-55 to +150	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

### THERMAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

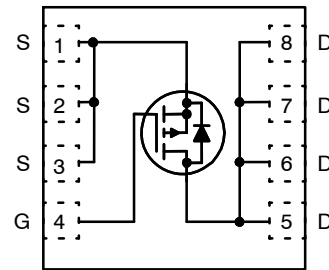
Symbol	Parameter	Value	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case	3.8	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1a)	53	$^\circ\text{C}/\text{W}$

$V_{DS}$	$R_{DS(on)}$ MAX	$I_D$ MAX
-20 V	6.5 mΩ @ -4.5 V	-56 A
	9.8 mΩ @ -2.5 V	
	20 mΩ @ -1.8 V	

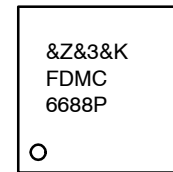


**PQFN8 3.3X3.3, 0.65P**  
**(Power 33)**  
**CASE 483AX**

### PIN ASSIGNMENT



### MARKING DIAGRAM



&Z = Assembly Plant Code  
&3 = 3-Digit Date-Code (YWW)  
&K = 2-Digit Lot Traceability Code  
FDMC6688P = Specific Device Code

### ORDERING INFORMATION

Device	Package	Shipping†
NTTFS007P02P8	PQFN8 (Power 33) (Pb-Free)	3,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

# NTTFS007P02P8

## ELECTRICAL CHARACTERISTICS (T<sub>J</sub> = 25°C unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
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### OFF CHARACTERISTICS

BV <sub>DSS</sub>	Drain to Source Breakdown Voltage	I <sub>D</sub> = -250 μA, V <sub>GS</sub> = 0 V	-20	-	-	V
ΔBV <sub>DSS</sub> / ΔT <sub>J</sub>	Breakdown Voltage Temperature Coefficient	I <sub>D</sub> = -250 μA, referenced to 25°C	-	-16	-	mV/°C
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> = -16 V, V <sub>GS</sub> = 0 V	-	-	-1	μA
I <sub>GSS</sub>	Gate to Source Leakage Current	V <sub>GS</sub> = ±8 V, V <sub>DS</sub> = 0 V	-	-	±100	nA

### ON CHARACTERISTICS

V <sub>GS(th)</sub>	Gate to Source Threshold Voltage	V <sub>GS</sub> = V <sub>DS</sub> , I <sub>D</sub> = -250 μA	-0.4	-0.75	-1	V
ΔV <sub>GS(th)</sub> / ΔT <sub>J</sub>	Gate to Source Threshold Voltage Temperature Coefficient	I <sub>D</sub> = -250 μA, referenced to 25°C	-	3	-	mV/°C
R <sub>DS(on)</sub>	Static Drain to Source On-Resistance	V <sub>GS</sub> = -4.5 V, I <sub>D</sub> = -14 A	-	5.3	6.5	mΩ
		V <sub>GS</sub> = -2.5 V, I <sub>D</sub> = -11 A	-	7	9.8	
		V <sub>GS</sub> = -1.8 V, I <sub>D</sub> = -9 A	-	10.7	20	
		V <sub>GS</sub> = -4.5 V, I <sub>D</sub> = -14 A, T <sub>J</sub> = 125°C	-	7.3	11	
g <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> = -5 V, I <sub>D</sub> = -14 A	-	80	-	S

### DYNAMIC CHARACTERISTICS

C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> = -10 V, V <sub>GS</sub> = 0 V, f = 1 MHz	-	4956	7435	pF
C <sub>oss</sub>	Output Capacitance		-	678	1020	pF
C <sub>rss</sub>	Reverse Transfer Capacitance		-	618	930	pF
R <sub>g</sub>	Gate Resistance		-	4.5	-	Ω

### SWITCHING CHARACTERISTICS

t <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> = -10 V, I <sub>D</sub> = -14 A, V <sub>GS</sub> = -4.5 V, R <sub>GEN</sub> = 6 Ω	-	19	35	ns
t <sub>r</sub>	Rise Time		-	33	53	ns
t <sub>d(off)</sub>	Turn-Off Delay Time		-	119	190	ns
t <sub>f</sub>	Fall Time		-	68	109	ns
Q <sub>g</sub>	Total Gate Charge	V <sub>DD</sub> = -10 V, I <sub>D</sub> = -14 A, V <sub>GS</sub> = -4.5 V	-	44	61	nC
Q <sub>gs</sub>	Gate to Source Charge		-	7.4	-	nC
Q <sub>gd</sub>	Gate to Drain "Miller" Charge		-	11	-	nC

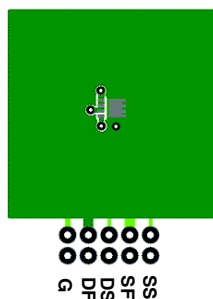
### DRAIN-SOURCE DIODE CHARACTERISTICS

V <sub>SD</sub>	Source to Drain Diode Forward Voltage	V <sub>GS</sub> = 0 V, I <sub>S</sub> = -14 A (Note 2)	-	-0.8	-1.2	V
		V <sub>GS</sub> = 0 V, I <sub>S</sub> = -2 A (Note 2)	-	-0.6	-1.2	
t <sub>rr</sub>	Reverse Recovery Time	I <sub>F</sub> = -14 A, di/dt = 100 A/μs	-	26	41	ns
Q <sub>rr</sub>	Reverse Recovery Charge		-	10	20	nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

#### NOTES:

- R<sub>θJA</sub> is determined with the device mounted on a 1 in<sup>2</sup> pad 2 oz copper pad on a 1.5 × 1.5 in. board of FR-4 material. R<sub>θJC</sub> is guaranteed by design while R<sub>θJA</sub> is determined by the user's board design.



- a. 53°C/W when mounted on a 1 in<sup>2</sup> pad of 2 oz copper.



- b. 125°C/W when mounted on a minimum pad of 2 oz copper.

- Pulse Test: Pulse Width < 300 μs, Duty cycle < 2.0 %.
- Pulse Id refers to Forward Bias Safe Operation Area.

TYPICAL CHARACTERISTICS

( $T_J = 25^\circ\text{C}$  Unless Otherwise Noted)

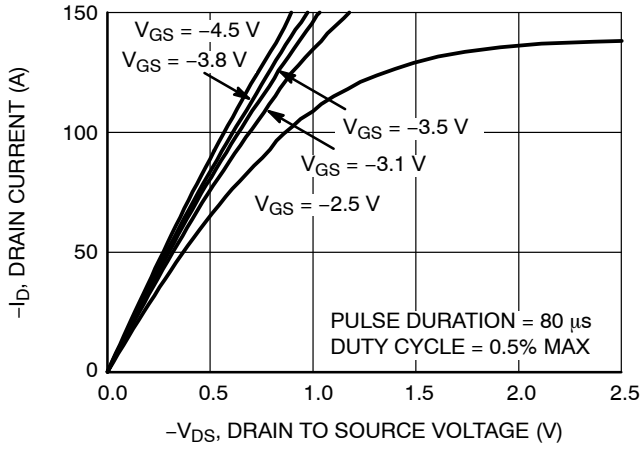


Figure 1. On-Region Characteristics

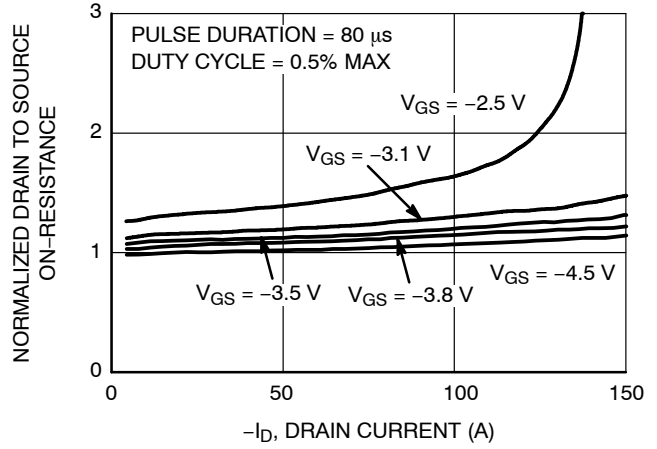


Figure 2. Normalized On-Resistance vs. Drain Current and Gate Voltage

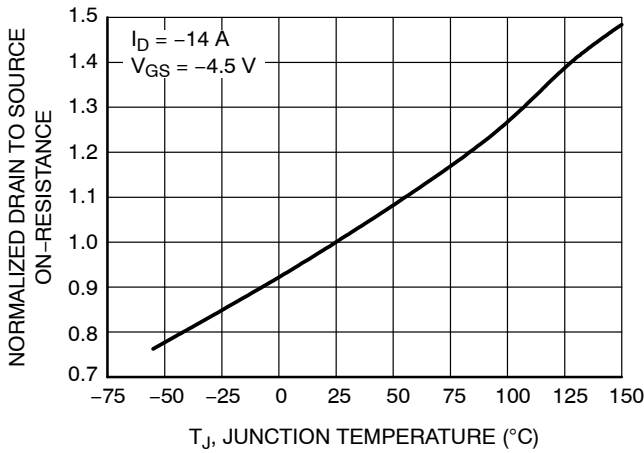


Figure 3. Normalized On-Resistance vs. Junction Temperature

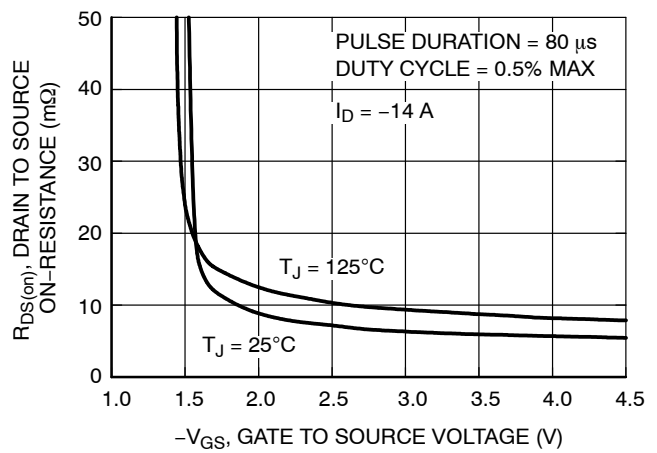


Figure 4. On-Resistance vs. Gate to Source Voltage

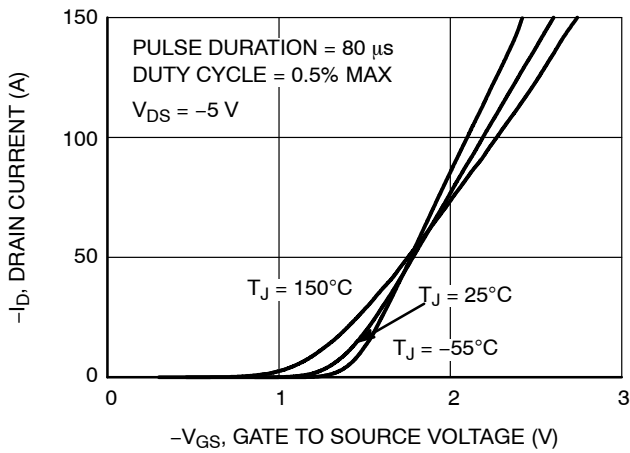


Figure 5. Transfer Characteristics

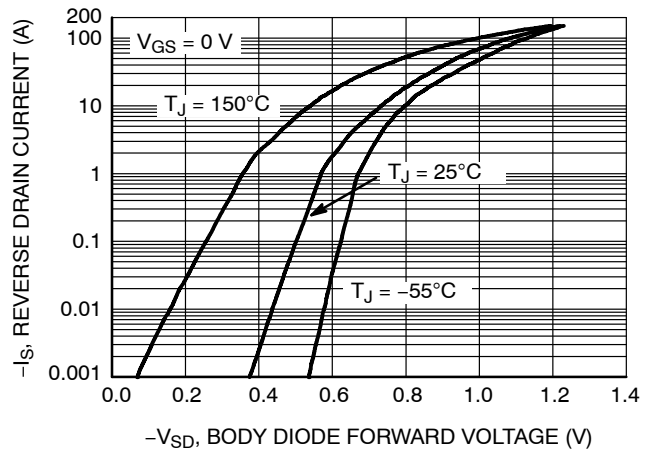


Figure 6. Source to Drain Diode Forward Voltage vs. Source Current

TYPICAL PERFORMANCE CHARACTERISTICS (CONTINUED)

( $T_J = 25^\circ\text{C}$  Unless Otherwise Noted)

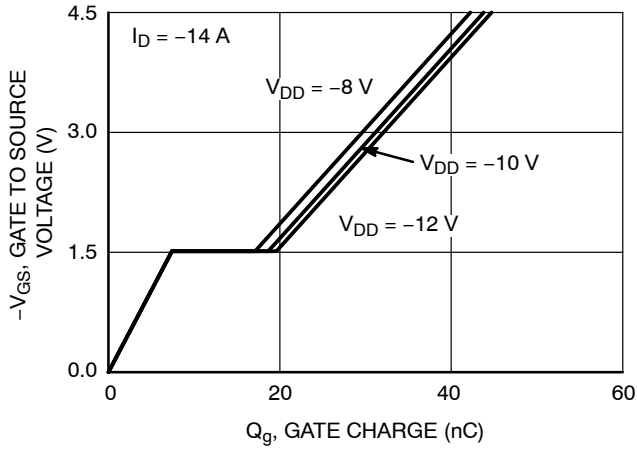


Figure 7. Gate Charge Characteristics

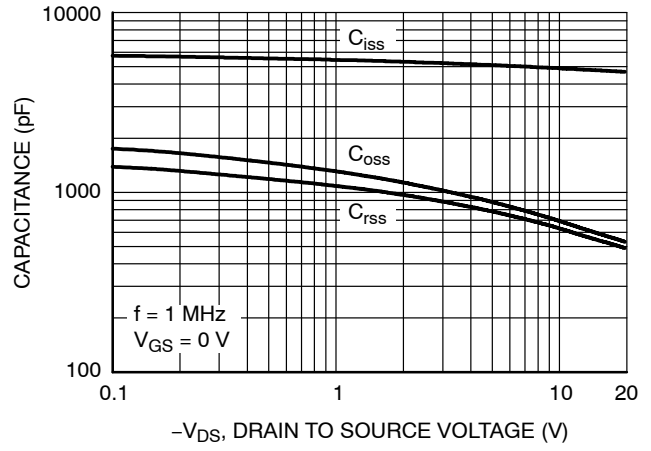


Figure 8. Capacitance vs. Drain to Source Voltage

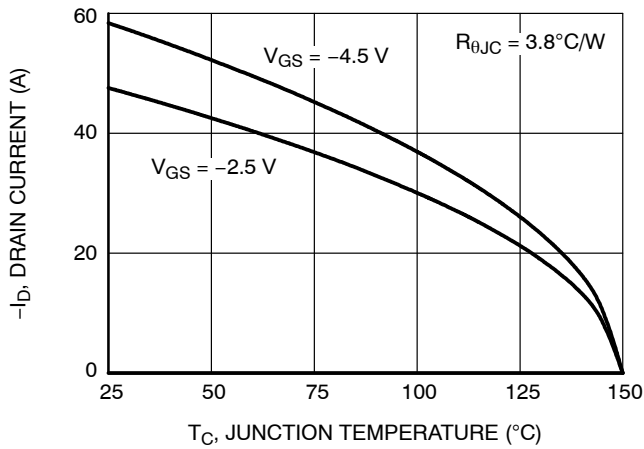


Figure 9. Maximum Continuous Drain Current vs. Case Temperature

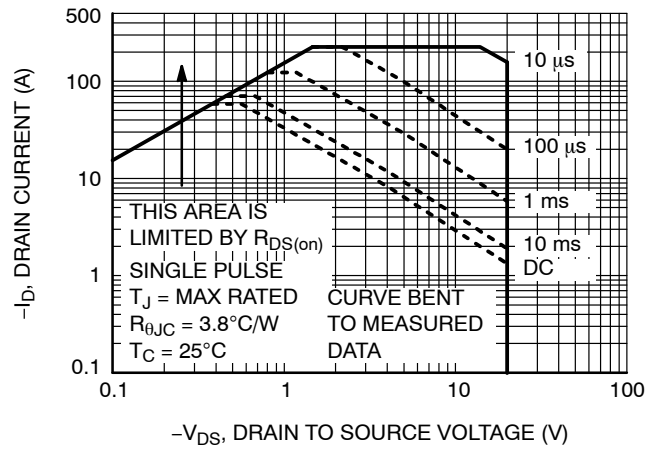


Figure 10. Forward Bias Safe Operating Area

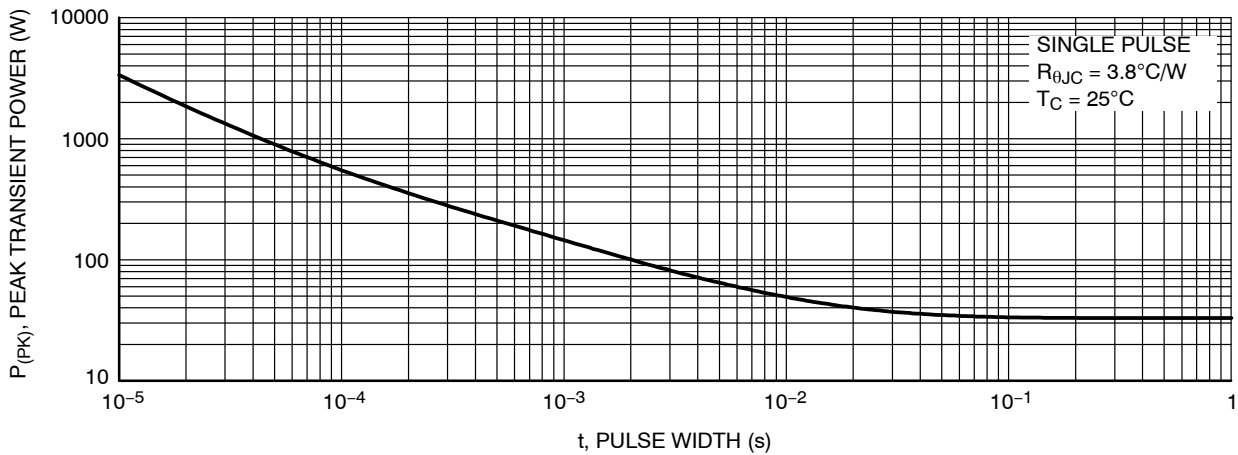


Figure 11. Single Pulse Maximum Power Dissipation

TYPICAL PERFORMANCE CHARACTERISTICS (CONTINUED)

( $T_J = 25^\circ\text{C}$  Unless Otherwise Noted)

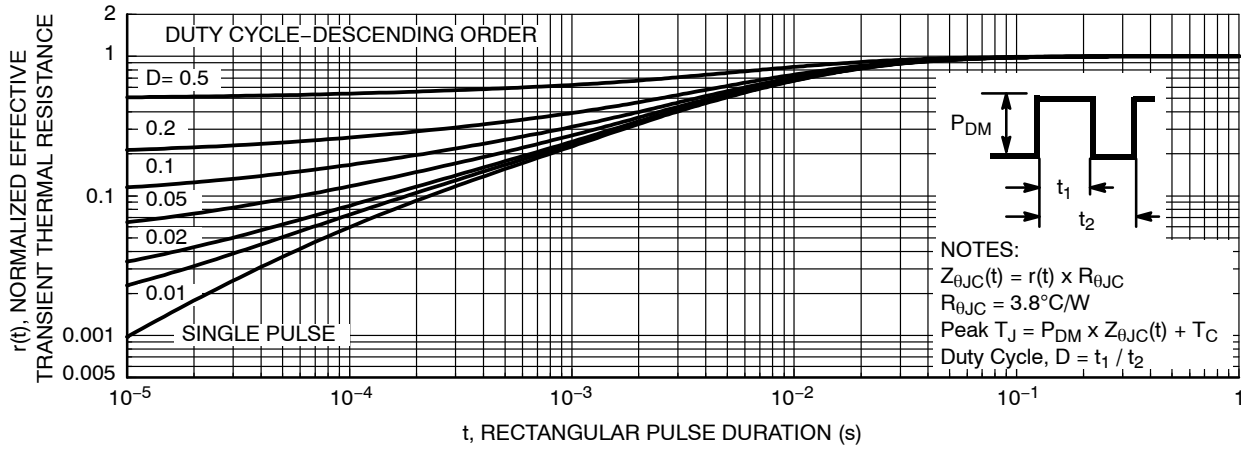
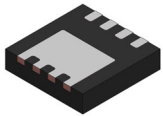
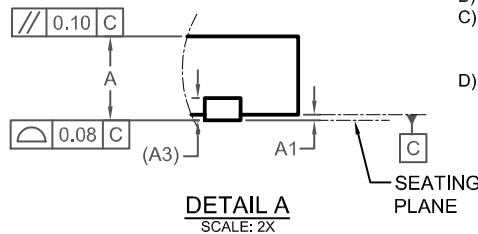
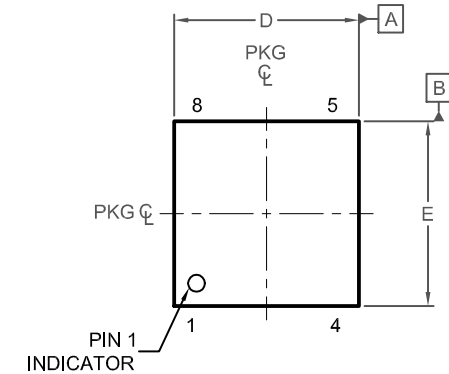


Figure 12. Junction-to-Case Transient Thermal Response Curve



**PQFN8 3.3X3.3, 0.65P**  
**CASE 483AX**  
**ISSUE B**

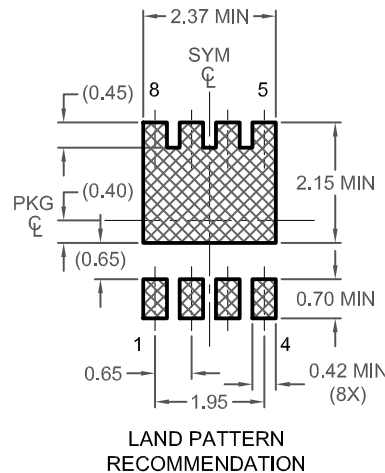
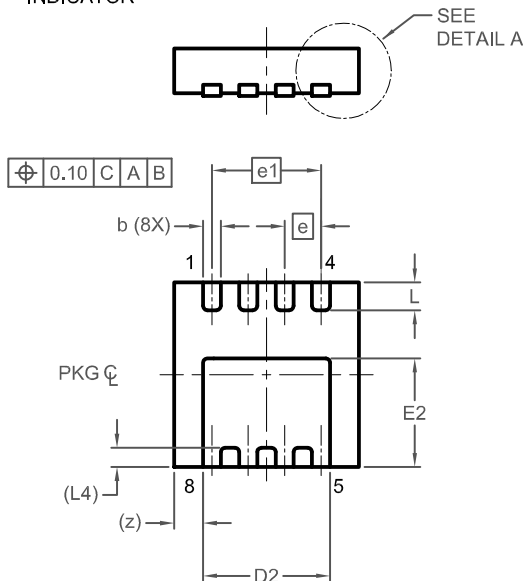
DATE 24 JUN 2022



NOTES: UNLESS OTHERWISE SPECIFIED

- A) PACKAGE STANDARD REFERENCE: JEDEC MO-240, ISSUE A, VAR. BA.
- B) ALL DIMENSIONS ARE IN MILLIMETERS.
- C) DIMENSIONS DO NOT INCLUDE BURRS OR MOLD FLASH. MOLD FLASH OR BURRS DOES NOT EXCEED 0.10MM.
- D) DIMENSIONING AND TOLERANCING PER ASME Y14.5M-2009.

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.70	0.75	0.80
A1	0.00	-	0.05
A3	0.20 REF		
b	0.27	0.32	0.37
D	3.20	3.30	3.40
D2	2.17	2.27	2.37
E	3.20	3.30	3.40
E2	1.84	1.94	2.04
e	0.65 BSC		
e1	1.95 BSC		
L	0.40	0.50	0.60
L4	0.34 REF		
z	0.52 REF		



\*FOR ADDITIONAL INFORMATION ON OUR PB-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

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